



■ 主要用途

高压高速电源开关。

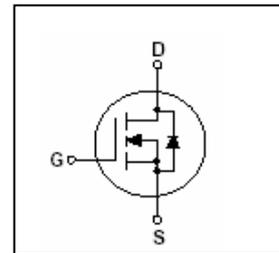
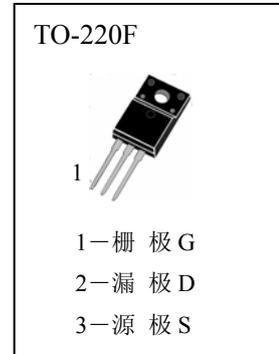
■ 极限值 (T_a=25°C)

T _{stg} ——贮存温度	-55~150°C
T _j ——结温	150°C
V _{DSS} ——漏极—源极电压	200V
V _{DGR} ——漏极—栅极电压(R _{GS} =20KΩ)	200V
V _{GS} ——栅极—源极电压	±20V
I _D ——*漏极电流(T _c =25°C)	18A
P _D ——耗散功率(T _c =25°C)	43W

*漏极电流受最大结温限制

■ 电参数 (T_a=25°C)

■ 外形图及引脚排列



参数符号	符号说明	最小值	典型值	最大值	单位	测试条件
BV _{DSS}	漏—源极击穿电压	200			V	I _D =250 μA, V _{GS} =0V
I _{DSS}	零栅压漏极电流			10	μA	V _{DS} =200V, V _{GS} =0
I _{GSS}	栅极泄漏电流			±100	nA	V _{GS} =±20V, V _{DS} =0V
V _{GS(th)}	栅—源极开启电压	2.0		4.0	V	V _{DS} =V _{GS} , I _D =250 μA
R _{DS(on)}	漏—源极导通电阻		0.145	0.18	Ω	V _{GS} =10V, I _D =9A
gfs	正向跨导		13		S	V _{DS} =40V, I _D =9A (注1)
C _{iss}	输入电容		1300	1700	pF	V _{DS} =25V, V _{GS} =0, f=1MHz
C _{oss}	输出电容		175	230	pF	
C _{rss}	反向传输电容		45	60	pF	
t _{d(on)}	导通延迟时间		20	50	nS	V _{DD} =100V, I _D =18A (峰值) R _G =25 Ω (注1)
t _r	上升时间		145	300	nS	
t _{d(off)}	断开延迟时间		145	300	nS	
t _f	下降时间		110	230	nS	
Q _g	栅极总电荷		45	58	nC	V _{DS} =0.8V _{DSS} V _{GS} =10V I _D =18A (注1)
Q _{gs}	栅极—源极电荷		6.5		nC	
Q _{gd}	栅极—漏极电荷		22		nC	
I _S	源极—漏极二极管正向电流			18	A	I _S =18A, V _{GS} =0
V _{SD}	源极—漏极二极管导通电压			1.5	V	
R _{th(j-c)}	热阻			2.89	°C/W	结到外壳

注：1、脉冲测试，宽度≤300 μS, 占空比≤2%



典型特性曲线

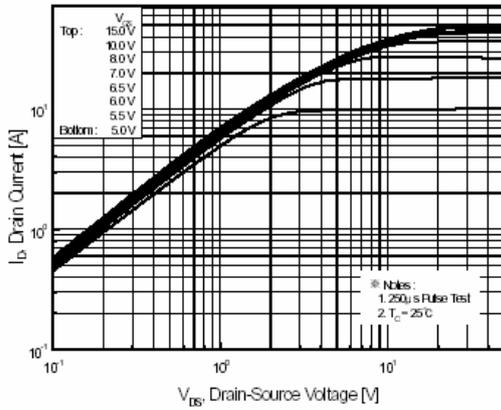


Figure 1. On-Region Characteristics

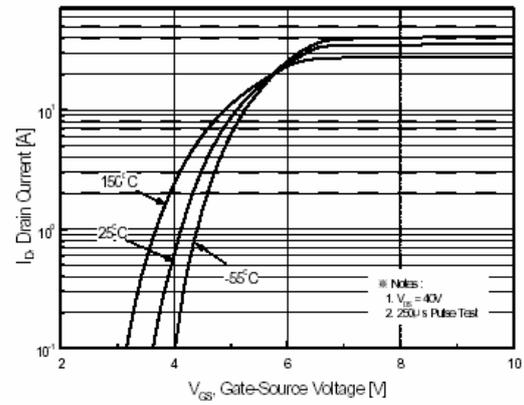


Figure 2. Transfer Characteristics

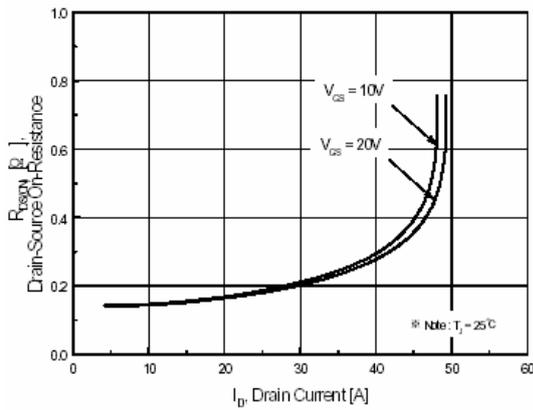


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

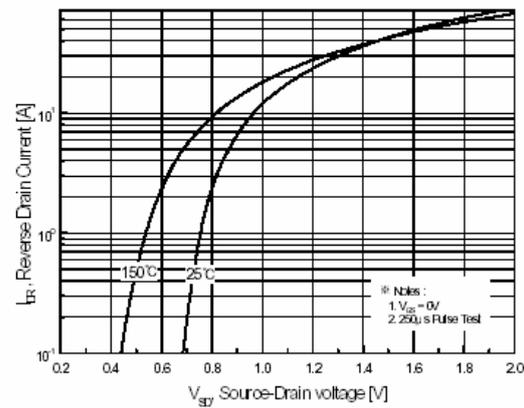


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

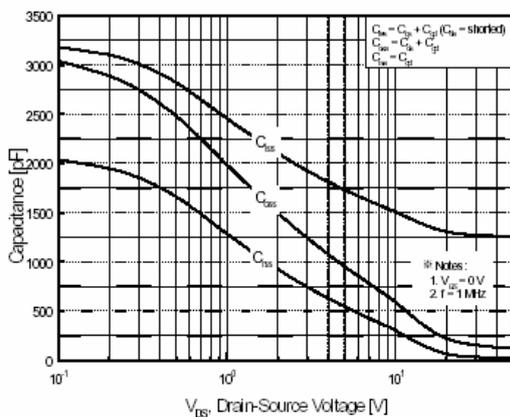


Figure 5. Capacitance Characteristics

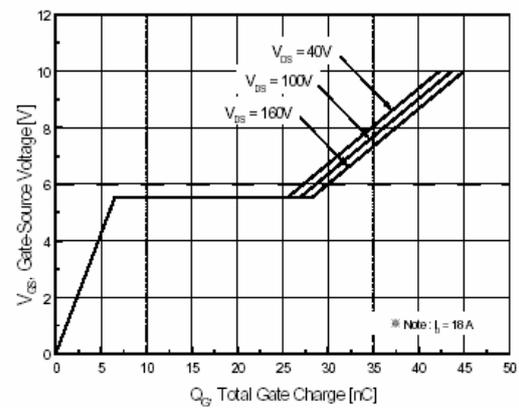


Figure 6. Gate Charge Characteristics



典型特性曲线

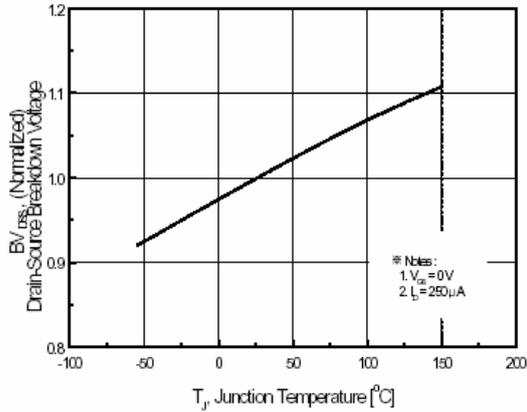


Figure 7. Breakdown Voltage Variation vs Temperature

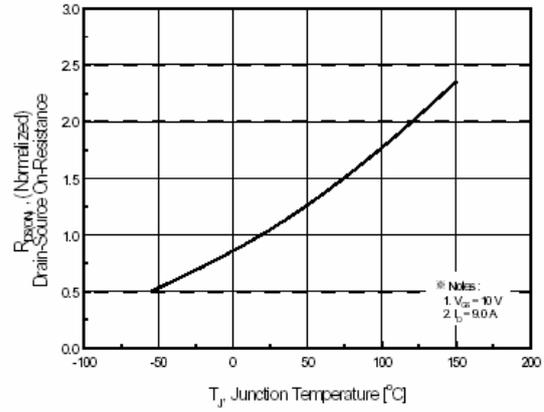


Figure 8. On-Resistance Variation vs Temperature

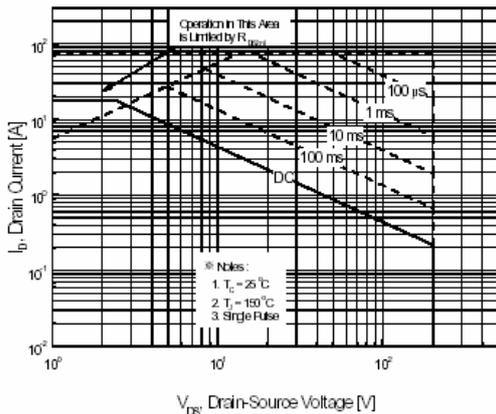


Figure 9 Maximum Safe Operating Area

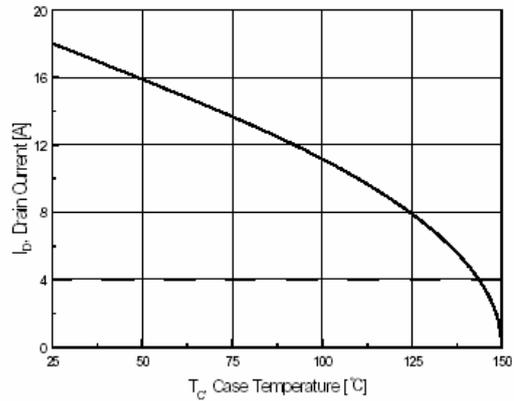


Figure 10. Maximum Drain Current vs Case Temperature

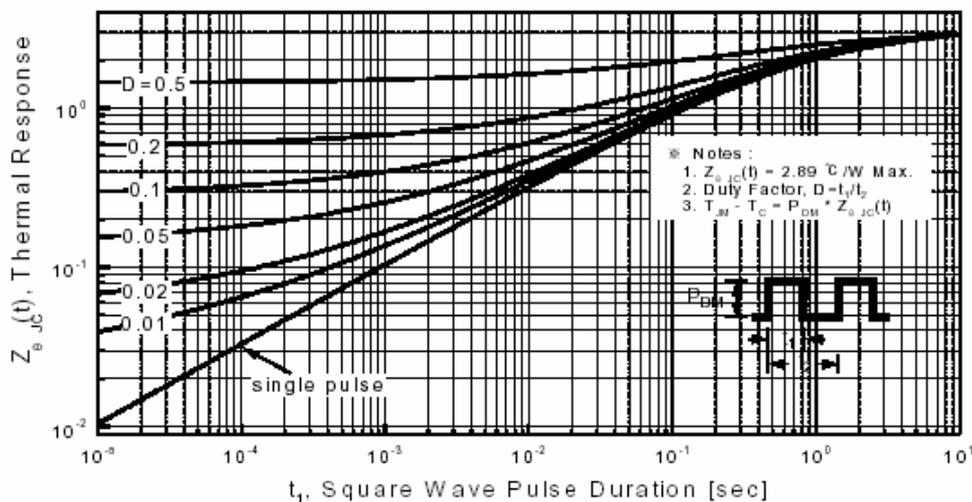
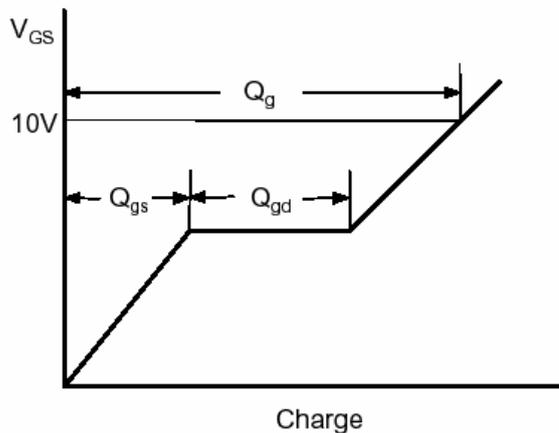
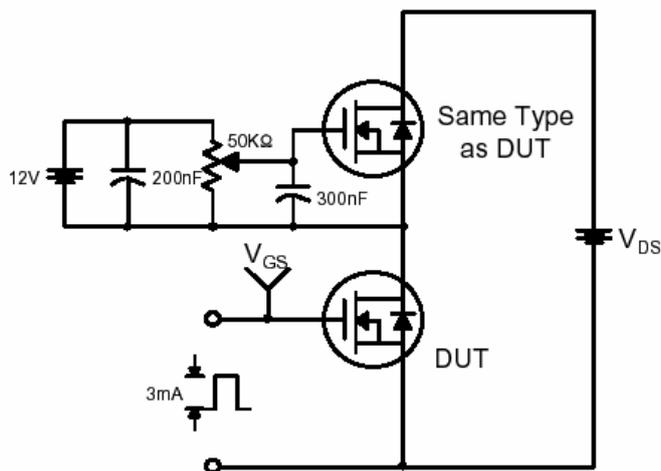


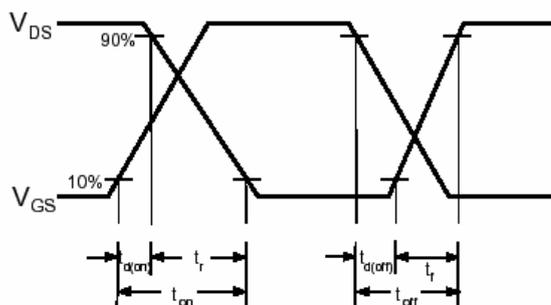
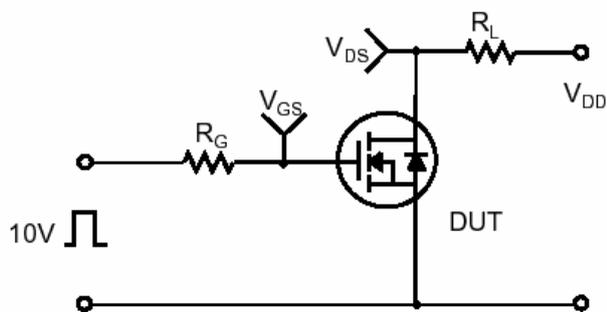
Figure 11 Transient Thermal Response Curve



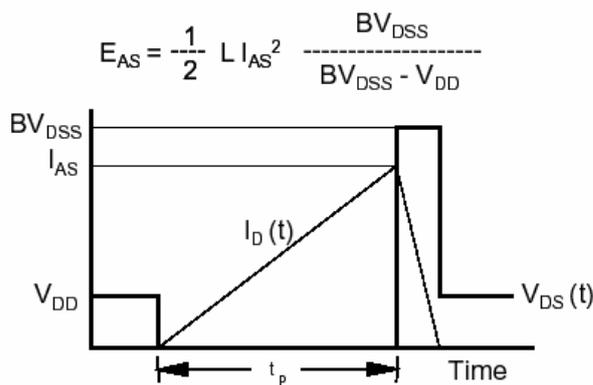
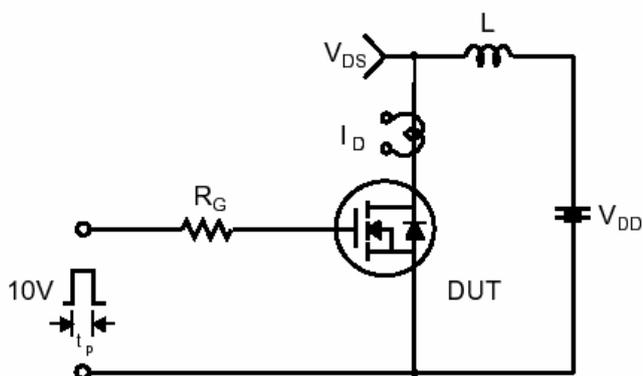
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

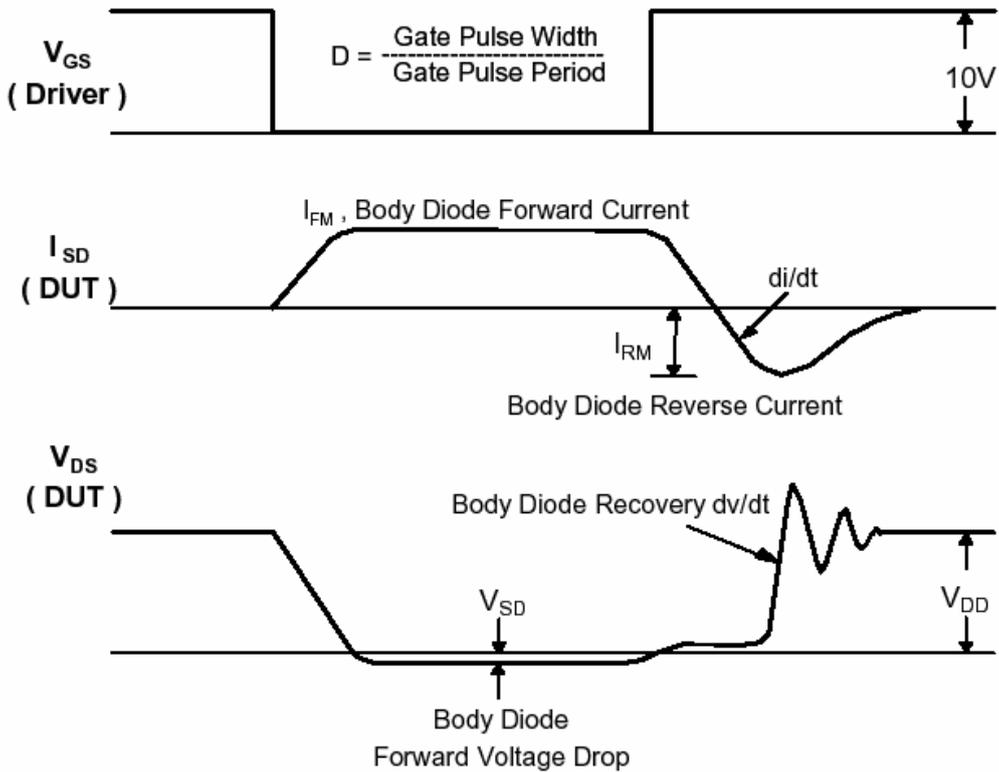
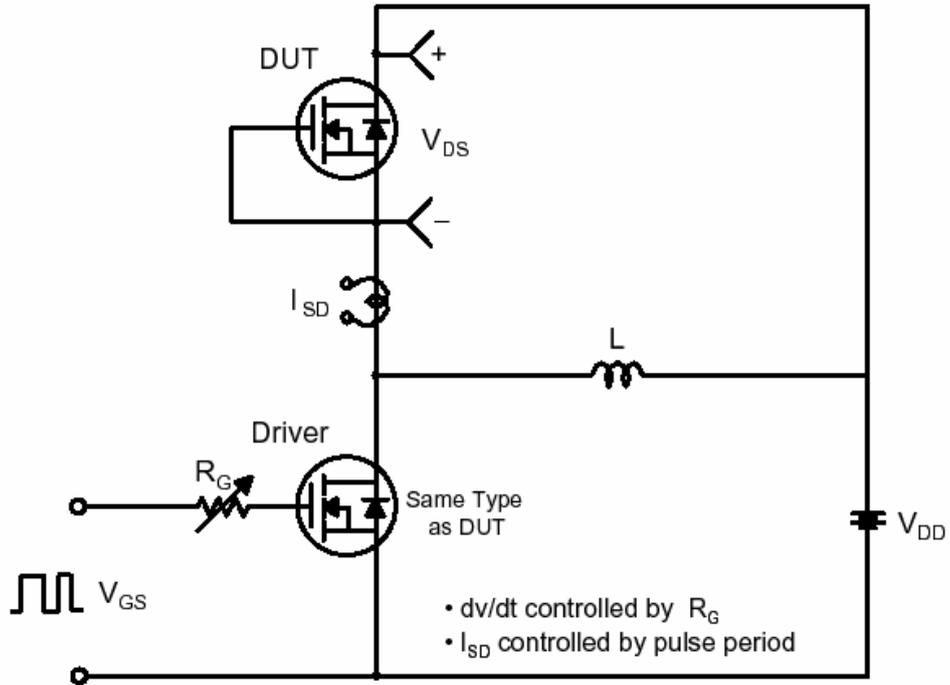


Unclamped Inductive Switching Test Circuit & Waveforms



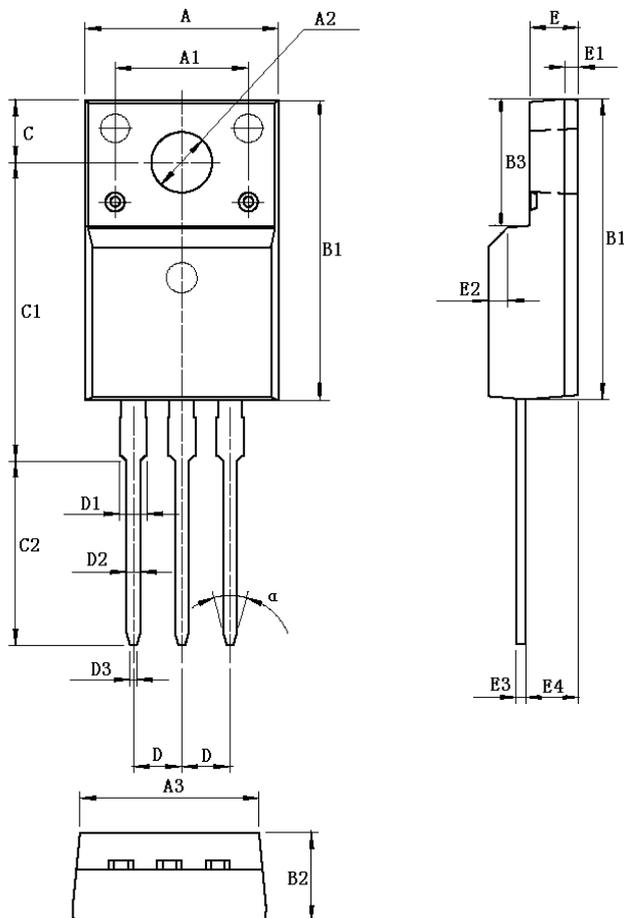


Peak Diode Recovery dv/dt Test Circuit & Waveforms





■ 外形尺寸图



(单位:mm)

尺寸 符号	Min	Max	尺 寸 符号	Min	Max	尺 寸 符号	Min	Max
A	9.96	10.36	C1	15.6	16.0	E2	(1.0×45°)	
A1		(7.0)	C2	9.55	9.95	E3	0.45	0.60
A2(Φ)	3.08	3.28	D	(2.54)		E4	2.56	2.96
A3	9.26	9.66	D1		1.47	α	(30°)	
B1	15.67	16.07	D2	0.7	0.9			
B2	4.5	4.9	D3	0.25	0.45			
B3	6.48	6.88	E	2.34	2.74			
C	3.2	3.4	E1	(0.7)				

注：()内的数值为参考数值